# STMicroelectronics - STM32F411VCT6TR Datasheet



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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	I <sup>2</sup> C, IrDA, LINbus, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I <sup>2</sup> S, POR, PWM, WDT
Number of I/O	81
Program Memory Size	256КВ (256К х 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f411vct6tr

Email: info@E-XFL.COM

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# 2.1 Compatibility with STM32F4 series

The STM32F411xC/xE are fully software and feature compatible with the STM32F4 series (STM32F42x, STM32F401, STM32F43x, STM32F41x, STM32F405 and STM32F407)

The STM32F411xC/xE can be used as drop-in replacement of the other STM32F4 products but some slight changes have to be done on the PCB board.









Figure 7. Startup in regulator OFF: slow V<sub>DD</sub> slope - power-down reset risen after V<sub>CAP 1</sub>/V<sub>CAP 2</sub> stabilization

1. This figure is valid whatever the internal reset mode (ON or OFF).



# Figure 8. Startup in regulator OFF mode: fast $V_{DD}$ slope - power-down reset risen before $V_{CAP\_1}/V_{CAP\_2}$ stabilization

1. This figure is valid whatever the internal reset mode (ON or OFF).



### 3.20.5 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source.

# 3.21 Inter-integrated circuit interface (I<sup>2</sup>C)

Up to three I<sup>2</sup>C bus interfaces can operate in multimaster and slave modes. They can support the standard (up to 100 kHz) and fast (up to 400 kHz) modes. The I2C bus frequency can be increased up to 1 MHz. For more details about the complete solution, please contact your local ST sales representative. They also support the 7/10-bit addressing mode and the 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

The devices also include programmable analog and digital noise filters (see Table 5).

	Analog filter	Digital filter
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2C peripheral clocks

# 3.22 Universal synchronous/asynchronous receiver transmitters (USART)

The devices embed three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART6).

These three interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. The USART1 and USART6 interfaces are able to communicate at speeds of up to 12.5 Mbit/s. The USART2 interface communicates at up to 6.25 bit/s.

USART1 and USART2 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller.





Figure 10. STM32F411xC/xE UFQFPN48 pinout

1. The above figure shows the package top view.



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	Iable 9. Alternate function mapping (continued)																
		AF00	AF01	AF02	AF03	AF04	AF05	AF06	AF07	AF08	AF09	AF10	AF11	AF12	AF13	AF14	AF15
	Port	SYS_AF	TIM1/TIM2	TIM3/ TIM4/ TIM5	TIM9/ TIM10/ TIM11	I2C1/I2C2/ I2C3	SPI1/I2S1S PI2/ I2S2/SPI3/ I2S3	SPI2/I2S2/ SPI3/ I2S3/SPI4/ I2S4/SPI5/ I2S5	SPI3/I2S3/ USART1/ USART2	USART6	12C2/ 12C3	OTG1_FS		SDIO			
	PB0	-	TIM1_CH2N	TIM3_CH3	-	-	-	SPI5_SCK /I2S5_CK		-	-	-	-	-	-	-	EVENT OUT
	PB1	-	TIM1_CH3N	TIM3_CH4	-	-	-	SPI5_NSS /I2S5_WS		-	-	-	-	-	-	-	EVENT OUT
	PB2	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PB3	JTDO- SWO	TIM2_CH2	-	-	-	SPI1_SCK/I 2S1_CK	SPI3_SCK /I2S3_CK	USART1_ RX	-	I2C2_SDA	-	-	-	-	-	EVENT OUT
	PB4	JTRST		TIM3_CH1	-	-	SPI1_MISO	SPI3_MISO	I2S3ext_S D	-	I2C3_SDA			SDIO_ D0	-	-	EVENT OUT
	PB5	-	-	TIM3_CH2	-	I2C1_SMB A	SPI1_MOSI /I2S1_SD	SPI3_MOSI/ I2S3_SD		-	-	-	-	SDIO_ D3	-	-	EVENT OUT
	PB6	-	-	TIM4_CH1	-	I2C1_SCL	-	-	USART1_ TX	-	-	-	-		-	-	EVENT OUT
t B	PB7	-	-	TIM4_CH2	-	I2C1_SDA	-	-	USART1_ RX	-	-	-	-	SDIO_ D0	-	-	EVENT OUT
Por	PB8	-	-	TIM4_CH3	TIM10_CH1	I2C1_SCL	-	SPI5_MOSI/ I2S5_SD	-	-	I2C3_SDA	-	-	SDIO_ D4	-	-	EVENT OUT
	PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS/I 2S2_WS	-	-	-	I2C2_SDA	-	-	SDIO_ D5	-	-	EVENT OUT
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK/I 2S2_CK	I2S3_MCK	-	-	-	-	-	SDIO_ D7	-	-	EVENT OUT
	PB11	-	TIM2_CH4	-	-	I2C2_SDA	I2S2_CKIN	-	-	-	-	-	-	-	-	-	EVENT OUT
	PB12	-	TIM1_BKIN	-	-	I2C2_SMB A	SPI2_NSS/I 2S2_WS	SPI4_NSS /I2S4_WS	SPI3_SCK /I2S3_CK	-	-	-	-	-	-	-	EVENT OUT
	PB13	-	TIM1_CH1N	-	-	-	SPI2_SCK/I 2S2_CK	SPI4_SCK/ I2S4_CK	-	-	-	-	-	-	-	-	EVENT OUT
	PB14	-	TIM1_CH2N	-	-	-	SPI2_MISO	I2S2ext_SD	-	-	-	-	-	SDIO_ D6	-	-	EVENT OUT
	PB15	RTC_50H z	TIM1_CH3N	-	-	-	SPI2_MOSI /I2S2_SD	-	-	-	-	-	-	SDIO_ CK	-	-	EVENT OUT

Pinouts and pin description

STM32F411xC STM32F411xE

STM32F411xC STM32F411xE

Pinouts and pin description

Port	AF00	AF01	AF02	AF03	AF04											I able 9. Alternate function mapping (continued)													
Port						AF05	AF06	AF07	AF08	AF09	AF10	AF11	AF12	AF13	AF14	AF15													
	SYS_AF	TIM1/TIM2	TIM3/ TIM4/ TIM5	TIM9/ TIM10/ TIM11	I2C1/I2C2/ I2C3	SPI1/I2S1S PI2/ I2S2/SPI3/ I2S3	SPI2/I2S2/ SPI3/ I2S3/SPI4/ I2S4/SPI5/ I2S5	SPI3/I2S3/ USART1/ USART2	USART6	12C2/ 12C3	OTG1_FS		SDIO																
PC0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT													
PC1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT													
PC2	-	-	-	-	-	SPI2_MISO	I2S2ext_SD	-	-	-	-	-	-	-	-	EVENT OUT													
PC3	-	-	-	-	-	SPI2_MOSI /I2S2_SD	-	-	-	-	-	-	-	-	-	EVENT OUT													
PC4	-	-	-	-	-		-	-	-	-	-	-	-	-	-	EVENT OUT													
PC5	-	-	-	-	-		-	-	-	-	-	-	-	-	-	EVENT OUT													
PC6	-	-	TIM3_CH1	-	-	I2S2_MCK	-	-	USART6_ TX	-	-	-	SDIO_ D6	-	-	EVENT OUT													
U PC7	-	-	TIM3_CH2	-	-	SPI2_SCK/I 2S2_CK	I2S3_MCK	-	USART6_ RX	-	-	-	SDIO_ D7	-	-	EVENT OUT													
PC8	-	-	TIM3_CH3	-	-	-	-	-	USART6_ CK	-	-	-	SDIO_ D0	-	-	EVENT OUT													
PC9	MCO_2	-	TIM3_CH4	-	I2C3_SDA	I2S2_CKIN	-	-		-	-	-	SDIO_ D1	-	-	EVENT OUT													
PC10	-	-	-	-	-	-	SPI3_SCK/I2 S3_CK	-	-	-	-	-	SDIO_ D2	-	-	EVENT OUT													
PC11	-	-	-	-	-	I2S3ext_SD	SPI3_MISO	-	-	-	-	-	SDIO_ D3	-	-	EVENT OUT													
PC12	-	-	-	-	-	-	SPI3_MOSI/I 2S3_SD	-	-	-	-	-	SDIO_ CK	-	-	EVENT OUT													
PC13	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-													
PC14	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-													
PC15	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-													

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Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states (f <sub>Flashmax</sub> )	Maximum Flash memory access frequency with wait states <sup>(1)(2)</sup>	I/O operation	Clock output frequency on I/O pins <sup>(3)</sup>	Possible Flash memory operations
V <sub>DD</sub> = 2.4 to 2.7 V	Conversion time up to 2.4 Msps	24 MHz	100 MHz with 4 wait states	<ul> <li>I/O compensation works</li> </ul>	up to 50 MHz	16-bit erase and program operations
V <sub>DD</sub> = 2.7 to 3.6 V <sup>(6)</sup>	Conversion time up to 2.4 Msps	30 MHz	100 MHz with 3 wait states	<ul> <li>I/O compensation works</li> </ul>	- up to 100 MHz when $V_{DD}$ = 3.0 to 3.6 V - up to 50 MHz when $V_{DD}$ = 2.7 to 3.0 V	32-bit erase and program operations

#### Table 15. Features depending on the operating power supply range (continued)

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.

- 2. Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.
- 3. Refer to Table 55: I/O AC characteristics for frequencies vs. external load.
- V<sub>DD</sub>/V<sub>DDA</sub> minimum value of 1.7 V, with the use of an external power supply supervisor (refer to Section 3.15.2: Internal reset OFF).
- 5. Prefetch is not available. Refer to AN3430 application note for details on how to adjust performance and power.
- The voltage range for the USB full speed embedded PHY can drop down to 2.7 V. However the electrical characteristics of D- and D+ pins will be degraded between 2.7 and 3 V.

# 6.3.2 VCAP\_1/VCAP\_2 external capacitors

Stabilization for the main regulator is achieved by connecting the external capacitor  $C_{EXT}$  to the VCAP\_1 and VCAP\_2 pins. For packages supporting only 1 VCAP pin, the 2 CEXT capacitors are replaced by a single capacitor.

C<sub>EXT</sub> is specified in *Table 16*.



1. Legend: ESR is the equivalent series resistance.

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Symbol			Тур					
	Conditions	Parameter	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	T <sub>A</sub> = 125 °C	Unit
	Flash in Stop mode, all	Main regulator usage	113.7	145 <sup>(2)</sup>	410	720 <sup>(2)</sup>	1217	
	independent watchdog	Low power regulator usage	43.1	68 <sup>(2)</sup>	310	600 <sup>(2)</sup>	1073	
IDD STOP	Flash in Deep power	Main regulator usage	76.2	105 <sup>(2)</sup>	320	600 <sup>(2)</sup>	1019	μA
_	down mode, all	Low power regulator usage	14	38 <sup>(2)</sup>	275	560 <sup>(2)</sup>	1025	
	independent watchdog	Low power low voltage regulator usage	10	30 <sup>(2)</sup>	235	510 <sup>(2)</sup>	928	

Table 28.	Typical and	d maximum	current	consumption	in Stop	mode -	V <sub>DD</sub> =3.6 V
	- <b>J</b>						

1. Guaranteed by characterization results.

2. Guaranteed by test in production.

Table 29. Typical and maximum current cor	nsumption in Standby mode - $V_{DD}$ = 1.7 V
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Symbol					Max <sup>(2</sup>	2)		
	Parameter	Conditions	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	T <sub>A</sub> = 125 °C	Unit
I <sub>DD_STBY</sub>	Supply current	Low-speed oscillator (LSE) and RTC ON	2.4	4	12	25	50	ıΔ
	in Standby mode	RTC and LSE OFF	1.8	3 <sup>(3)</sup>	11	24 <sup>(3)</sup>	49	μΛ

1. When the PDR is OFF (internal reset is OFF), the typical current consumption is reduced by 1.2  $\mu$ A.

2. Guaranteed by characterization results.

3. Guaranteed by test in production.

## Table 30. Typical and maximum current consumption in Standby mode - $\rm V_{DD}$ = 3.6 V

Symbol		Conditions			Max <sup>(2</sup>	2)		
	Parameter			T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	T <sub>A</sub> = 125 °C	Unit
I <sub>DD_STBY</sub>	Supply current in Standby mode	Low-speed oscillator (LSE) and RTC ON	2.8	5	14	29	59	
		RTC and LSE OFF	2.1	4 <sup>(3)</sup>	13.5	28 <sup>(3)</sup>	58	μA

1. When the PDR is OFF (internal reset is OFF), the typical current consumption is reduced by 1.2  $\mu$ A.

2. Guaranteed by characterization results.

3. Guaranteed by test in production.



Symbol				Тур						
	Parameter	Conditions <sup>(1)</sup>		<sub>A</sub> = 25 °	С	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	T <sub>A</sub> = 125 °C	Unit	
			V <sub>BAT</sub> = 1.7 V	V <sub>BAT</sub> = 2.4 V	V <sub>BAT</sub> = 3.3 V	V <sub>E</sub>	<sub>3AT</sub> = 3.6	; V		
I <sub>DD_VBAT</sub>	Backup domain supply current	Low-speed oscillator (LSE in low- drive mode) and RTC ON	0.7	0.8	1.0	3	5	6.8		
		Low-speed oscillator (LSE in high- drive mode) and RTC ON	1.5	1.6	1.9	3.8	5.8	8.6	μA	
		RTC and LSE OFF	0.1	0.1	0.1	2	4	5.8		

Table 31. Typical and maximum current consumptions in  $V_{\text{BAT}}\xspace$  mode

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a  $\rm C_L$  of 6 pF for typical values.

2. Guaranteed by characterization results.



Figure 20. Typical V<sub>BAT</sub> current consumption (LSE in low-drive mode and RTC ON)



Perij	Peripheral		Unit
	TIM1	5.71	
	TIM9	2.86	
	TIM10	1.79	
	TIM11	2.02	
	OTG_FS	23.93	
APB2	ADC1 <sup>(4)</sup>	2.98	
(up to 100 MHz)	SPI1	1.19	μΑνινίπΖ
	USART1	3.10	
	USART6	2.86	
	SDIO	5.95	
	SPI4	1.31	
	SYSCFG	0.71	

 Table 33. Peripheral current consumption (continued)

1. Valid if all the DMA streams are activated (please refer to the reference manual RM0383).

2. For N DMA streams activated (up to 8 activated streams, refer to the reference manual RM0383).

3. I2SMOD bit set in SPI\_I2SCFGR register, and then the I2SE bit set to enable I2S peripheral.

4. When the ADC is ON (ADON bit set in the ADC\_CR2 register), add an additional power consumption of 1.6 mA for the analog part.



Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
V <sub>prog</sub>	Programming voltage		2.7	-	3.6	V
V <sub>PP</sub>	V <sub>PP</sub> voltage range		7	-	9	V
I <sub>PP</sub>	Minimum current sunk on the $V_{\rm PP}$ pin		10	-	-	mA
t <sub>VPP</sub> <sup>(3)</sup>	Cumulative time during which $V_{PP}$ is applied		-	-	1	hour

 Table 46. Flash memory programming with V<sub>PP</sub> voltage (continued)

1. Guaranteed by design.

2. The maximum programming time is measured after 100K erase operations.

3.  $V_{PP}$  should only be connected during programming/erasing.

Symbol	Paramotor	Conditions	Value	Unit
Symbol	Falameter	Conditions	Min <sup>(1)</sup>	Unit
N <sub>END</sub>	Endurance	$T_A = -40 \text{ to } + 85 \text{ °C} \text{ (temp. range 6)}$ $T_A = -40 \text{ to } + 105 \text{ °C} \text{ (temp. range 7)}$ $T_A = -40 \text{ to } + 125 \text{ °C} \text{ (temp. range 3)}$	10	kcycles
t <sub>RET</sub> Data retention		1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 85 °C	30	
	Data rotantian	1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 105 °C	10	Vooro
	Data retention	1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 125 °C	3	
		10 kcycle <sup>(2)</sup> at T <sub>A</sub> = 55 °C	20	

Table 47. Flash memo	y endurance and o	data retention

1. Guaranteed by characterization results.

2. Cycling performed over the whole temperature range.

### 6.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

### Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A burst of fast transient voltage (positive and negative) is applied to V<sub>DD</sub> and V<sub>SS</sub> through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 49*. They are based on the EMS levels and classes defined in application note AN1709.



### 6.3.18 TIM timer characteristics

The parameters given in Table 57 are guaranteed by design.

Refer to Section 6.3.16: I/O port characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Symbol	Parameter	Conditions <sup>(3)</sup>	Min	Max	Unit
		AHB/APBx prescaler=1	1	-	t <sub>TIMxCLK</sub>
trac(TIM)	Timer resolution time	100 MHz	11.9	-	ns
res(TIM)		AHB/APBx prescaler>4,	1	-	t <sub>TIMxCLK</sub>
		f <sub>TIMxCLK</sub> = 100 MHz	11.9	-	ns
f Timer external clock			0	f <sub>TIMxCLK</sub> /2	MHz
'EXT	frequency on CH1 to CH4	f <sub>TIMxCLK</sub> = 100 MHz	0	50	MHz
Res <sub>TIM</sub>	Timer resolution		-	16/32	bit
t <sub>COUNTER</sub>	16-bit counter clock period when internal clock is selected	f <sub>TIMxCLK</sub> = 100 MHz	0.0119	780	μs
t <sub>MAX_COUNT</sub>	Maximum possible count		-	65536 × 65536	t <sub>TIMxCLK</sub>
		f <sub>TIMxCLK</sub> = 100 MHz	-	51.1	S

Table 57. TIMx characteristics<sup>(1)(2)</sup>

1. TIMx is used as a general term to refer to the TIM1 to TIM11 timers.

2. Guaranteed by design.

 The maximum timer frequency on APB1 is 50 MHz and on APB2 is up to 100 MHz, by setting the TIMPRE bit in the RCC\_DCKCFGR register, if APBx prescaler is 1 or 2 or 4, then TIMxCLK = HCKL, otherwise TIMxCLK >= 4x PCLKx.

# 6.3.19 Communications interfaces

### I<sup>2</sup>C interface characteristics

The I<sup>2</sup>C interface meets the requirements of the standard I<sup>2</sup>C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not "true" opendrain. When configured as open-drain, the PMOS connected between the I/O pin and V<sub>DD</sub> is disabled, but is still present.

The I<sup>2</sup>C characteristics are described in *Table 58*. Refer also to *Section 6.3.16*: I/O port *characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).

The I<sup>2</sup>C bus interface supports standard mode (up to 100 kHz) and fast mode (up to 400 kHz). The I<sup>2</sup>C bus frequency can be increased up to 1 MHz. For more details about the complete solution, please contact your local ST sales representative.



Symbol	Parameter	Standard mode I <sup>2</sup> C <sup>(1)(2)</sup>		Fast mode I <sup>2</sup> C <sup>(1)(2)</sup>		Unit
		Min	Max	Min	Max	
t <sub>w(SCLL)</sub>	SCL clock low time	4.7	-	1.3	-	110
t <sub>w(SCLH)</sub>	SCL clock high time	4.0	-	0.6	-	μο
t <sub>su(SDA)</sub>	SDA setup time	250	-	100	-	
t <sub>h(SDA)</sub>	SDA data hold time	0	3450 <sup>(3)</sup>	0	900 <sup>(4)</sup>	
t <sub>r(SDA)</sub> t <sub>r(SCL)</sub>	SDA and SCL rise time	-	1000	-	300	ns
t <sub>f(SDA)</sub> t <sub>f(SCL)</sub>	SDA and SCL fall time	-	300	-	300	
t <sub>h(STA)</sub>	Start condition hold time	4.0	-	0.6	-	
t <sub>su(STA)</sub>	Repeated Start condition setup time	4.7	-	0.6	-	μs
t <sub>su(STO)</sub>	Stop condition setup time	4.0	-	0.6	-	μs
t <sub>w(STO:STA)</sub>	Stop to Start condition time (bus free)	4.7	-	1.3	-	μs
t <sub>SP</sub>	Pulse width of the spikes that are suppressed by the analog filter for standard fast mode	0	50 <sup>(5)</sup>	0	50 <sup>(5)</sup>	ns
Cb	Capacitive load for each bus line	-	400	-	400	pF

Table 58. I<sup>2</sup>C characteristics

1. Guaranteed by design.

f<sub>PCLK1</sub> must be at least 2 MHz to achieve standard mode I<sup>2</sup>C frequencies. It must be at least 4 MHz to achieve fast mode I<sup>2</sup>C frequencies, and a multiple of 10 MHz to reach the 400 kHz maximum I<sup>2</sup>C fast mode clock.

3. The device must internally provide a hold time of at least 300 ns for the SDA signal in order to bridge the undefined region of the falling edge of SCL.

4. The maximum data hold time has only to be met if the interface does not stretch the low period of SCL signal.

5. The minimum width of the spikes filtered by the analog filter is above  $t_{\text{SP}} \, (\text{max})$ 





Figure 35. SPI timing diagram - slave mode and CPHA =  $1^{(1)}$ 







#### **Electrical characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t. (2)	Injection trigger conversion	f <sub>ADC</sub> = 30 MHz	-	-	0.100	μs
4at` ´	latency		-	-	3 <sup>(5)</sup>	1/f <sub>ADC</sub>
t. (2)	Regular trigger conversion	f <sub>ADC</sub> = 30 MHz	-	-	0.067	μs
Jatr	latency		-	-	2 <sup>(5)</sup>	1/f <sub>ADC</sub>
to <sup>(2)</sup>	Sampling time	f <sub>ADC</sub> = 30 MHz	0.100	-	16	μs
is			3	-	480	1/f <sub>ADC</sub>
t <sub>STAB</sub> <sup>(2)</sup>	Power-up time		-	2	3	μs
		f <sub>ADC</sub> = 30 MHz 12-bit resolution	0.50	-	16.40	μs
t <sub>CONV</sub> <sup>(2)</sup> Total co samplir	Total conversion time (including sampling time)	f <sub>ADC</sub> = 30 MHz 10-bit resolution	0.43	-	16.34	μs
		f <sub>ADC</sub> = 30 MHz 8-bit resolution	0.37	-	16.27	μs
		f <sub>ADC</sub> = 30 MHz 6-bit resolution	0.30	-	16.20	μs
		9 to 492 (t <sub>S</sub> for sampling +n-bit resolution for successive approximation)				
		12-bit resolution Single ADC	-	-	2	Msps
f <sub>S</sub> <sup>(2)</sup>	Sampling rate (f <sub>ADC</sub> = 30 MHz, and	12-bit resolution Interleave Dual ADC mode	-	-	3.75	Msps
		12-bit resolution Interleave Triple ADC mode	-	-	6	Msps
I <sub>VREF+</sub> <sup>(2)</sup>	ADC V <sub>REF</sub> DC current consumption in conversion mode		-	300	500	μA
I <sub>VDDA</sub> <sup>(2)</sup>	ADC V <sub>DDA</sub> DC current consumption in conversion mode		-	1.6	1.8	mA

#### Table 65. ADC characteristics (continued)

1. V<sub>DDA</sub> minimum value of 1.7 V is possible with the use of an external power supply supervisor (refer to Section 3.15.2: Internal reset OFF).

2. Guaranteed by characterization results.

3.  $V_{REF+}$  is internally connected to  $V_{DDA}$  and  $V_{REF-}$  is internally connected to  $V_{SSA}$ .

4.  $R_{ADC}$  maximum value is given for V<sub>DD</sub>=1.7 V, and minimum value for V<sub>DD</sub>=3.3 V.

5. For external triggers, a delay of  $1/f_{PCLK2}$  must be added to the latency specified in *Table 65*.



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Cumhal		millimeters inches <sup>(1)</sup>				
Зутрог	Min	Тур	Мах	Min	Тур	Мах
А	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3 <sup>(2)</sup>	-	0.025	-	-	0.0010	-
b <sup>(3)</sup>	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	2.964	2.999	3.034	0.1167	0.1181	0.1194
E	3.150	3.185	3.220	0.1240	0.1254	0.1268
е	-	0.400	-	-	0.0157	-
e1	-	2.400	-	-	0.0945	-
e2	-	2.400	-	-	0.0945	-
F	-	0.2995	-	-	0.0118	-
G	-	0.3925	-	-	0.0155	-
ааа	-	0.100	-	-	0.0039	-
bbb	-	0.100	-	-	0.0039	-
CCC	-	0.100	-	-	0.0039	-
ddd	-	0.050	-	-	0.0020	-
eee	-	0.050	-	-	0.0020	-

# Table 79. WLCSP49 - 49-ball, 2.999 x 3.185 mm, 0.4 mm pitch wafer level chip scalepackage mechanical data

1. Values in inches are converted from mm and rounded to 4 decimal digits.

2. Back side coating

3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

# Figure 47. WLCSP49 - 49-ball, 2.999 x 3.185 mm, 0.4 mm pitch wafer level chip scale recommended footprint





### **Device marking for LQFP100**

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



# Table 84. UFBGA100, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array packagemechanical data (continued)

Symbol	millimeters			inches <sup>(1)</sup>		
Зупрог	Min.	Тур.	Max.	Min.	Тур.	Max.
ddd	-	-	0.100	-	-	0.0039
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

#### Figure 59. Recommended PCB design rules for pads (0.5 mm-pitch BGA)



1. Non solder mask defined (NSMD) pads are recommended.

2. 4 to 6 mils solder paste screen printing process.





# Appendix A Recommendations when using the internal reset OFF

When the internal reset is OFF, the following integrated features are no longer supported:

- The integrated power-on-reset (POR)/power-down reset (PDR) circuitry is disabled.
- The brownout reset (BRO) circuitry must be disabled. By default BOR is OFF.
- The embedded programmable voltage detector (PVD) is disabled.
- V<sub>BAT</sub> functionality is no more available and VBAT pin should be connected to V<sub>DD</sub>.

# A.1 Operating conditions

#### Table 87. Limitations depending on the operating power supply range

Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait state (f <sub>Flashmax</sub> )	Maximum Flash memory access frequency with no wait states <sup>(1) (2)</sup>	I/O operation	Possible Flash memory operations
V <sub>DD</sub> = 1.7 to 2.1 V <sup>(3)</sup>	Conversion time up to 1.2 Msps	20 MHz <sup>(4)</sup>	100 MHz with 6 wait states	No I/O compensation	8-bit erase and program operations only

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.

 Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.

3. V<sub>DD</sub>/V<sub>DDA</sub> minimum value of 1.7 V, with the use of an external power supply supervisor (refer to Section 3.15.1: Internal reset ON).

4. Prefetch is not available. Refer to AN3430 application note for details on how to adjust performance and power.



# **Revision history**

Date	Revision	Changes		
19-Jun-2014	1	Initial release.		
		Introduced the BAM feature in <i>Features</i> , <i>Section 2: Description.</i> , and <i>Section 3.3: Batch Acquisition mode (BAM)</i> .		
		Updated Section 3.5: Embedded Flash memory, Section 3.14: Power supply schemes and Section 3.18: Low-power modes, Section 3.20.2: General-purpose timers (TIMx) and Section 3.30: Temperature sensor.		
		Modified Table 8: STM32F411xC/xE pin definitions, Table 9: Alternate function mapping and APB2 in Table 10: STM32F411xC/xE register boundary addresses.		
10-Sep-2014	2	Modified Table 34: Low-power mode wakeup timings(1), Table 20: Typical and maximum current consumption, code with data processing (ART accelerator disabled) running from SRAM - VDD = 1.7 V, Table 21: Typical and maximum current consumption, code with data processing (ART accelerator disabled) running from SRAM - VDD = 3.6 V, Table 25: Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled with prefetch) running from Flash memory - VDD = 3.6 V, Table 26: Typical and maximum current consumption in Sleep mode - VDD = 3.6 V and Table 58: I2C characteristics and Figure 33: I2C bus AC waveforms and measurement circuit		
		Added Figure 21: Low-power mode wakeup, Section Appendix A: Recommendations when using the internal reset OFF and Section Appendix B: Application block diagrams.		
		Changed datasheet status to Production Data.		
		Updated Table 31: Typical and maximum current consumptions in VBAT mode.		
		Section : On-chip peripheral current consumption: changed HCLK frequency and updated DMA1 and DMA2 current consumption in <i>Table 33: Peripheral current consumption</i> .		
		Updated Table 55: I/O AC characteristics.		
		Updated THD in Table 69: ADC dynamic accuracy at fADC = 18 MHz - limited test conditions and Table 70: ADC dynamic accuracy at fADC = 36 MHz - limited test conditions.		
27-Nov-2014	3	Updated Table 55: I/O AC characteristics.		
		Updated Figure 46: WLCSP49 - 49-ball, 2.999 x 3.185 mm, 0.4 mm pitch wafer level chip scale package outline and Figure 48: WLCSP49 marking (package top view). Added Figure 47: WLCSP49 - 49-ball, 2.999 x 3.185 mm, 0.4 mm pitch wafer level chip scale recommended footprint and Table 80: WLCSP49 recommended PCB design rules (0.4 mm pitch).		
		Updated Figure 51: UFQFPN48 marking example (package top view), Figure 54: LQFP64 marking example (package top view), Figure 57: LQPF100 marking example (package top view), and Figure 58: UFBGA100 - 100-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline.		
		Added VPP alternate function for BOOT0 in <i>Table 8: STM32F411xC/xE pin definitions</i> .		
04-Feb-2015	4	Added TC inputs in Table 11: Voltage characteristics, Table 12: Current characteristics, Table 14: General operating conditions, Table 53: I/O static characteristics and Figure 30: FT/TC I/O input characteristics.		
		Updated V <sub>ESD(CDM)</sub> in <i>Table 50: ESD absolute maximum ratings</i> .		
		A3 minimum and maximum values removed in <i>Table 83: UFBGA100 - 100-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data.</i>		

Table 88.	Document	revision	history
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